AP30P06DF

-60V P-Channel Enhancement Mode MOSFET

Description

The AP30P06DF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

V_{DS} = -60V I_D =-30A

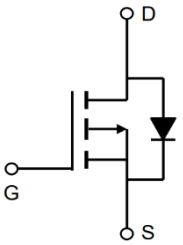
$R_{DS(ON)}$ < 35mΩ @ V_{GS}=-10V **(Type：28mΩ)**

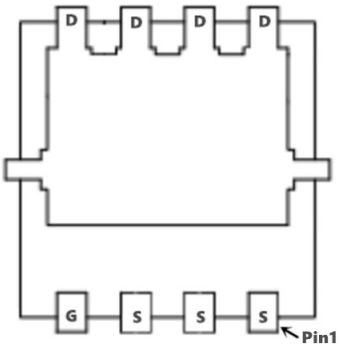
Application

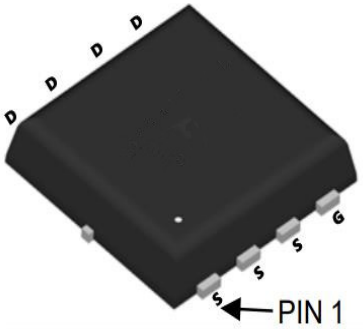
Lithium battery protection

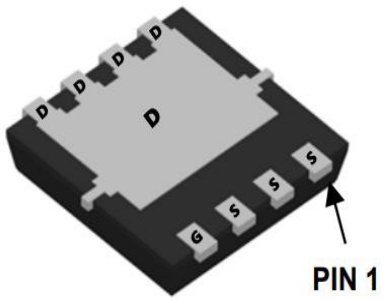
Wireless impact

Mobile phone fast charging









Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP30P06DF	PDFN3*3-8L	AP30P06DF XXX YYYY	5000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-60	V
VGS	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, -V_{GS} @ -10V[1]	-30	A
I_D@T_C=100℃	Continuous Drain Current, -V_{GS} @ -10V[1]	-27	A
IDM	Pulsed Drain Current[2]	-85	A
EAS	Single Pulse Avalanche Energy[3]	113	mJ
IAS	Avalanche Current	47.6	A
P_D@T_C=25℃	Total Power Dissipation[4]	52.1	W
TSTG	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta}JA$	Thermal Resistance Junction-Ambient [1]	85	℃/W
$R_{\theta}JC$	Thermal Resistance Junction-Case[1]	2.4	℃/W

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Electrical Characteristics (T_C=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-60	-68	---	V
△BVDSS/△TJ	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.035	---	V/℃
RDS(ON)	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-10A	---	28	35	mΩ
		V_{GS}=-4.5V , I_D=-8A	---	33	38	
VGS(th)	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	-1.6	-2.5	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.28	---	mV/℃
IDSS	Drain-Source Leakage Current	V_{DS}=-48V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=-48V , V_{GS}=0V , T_J=55℃	---	---	5	
IGSS	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-18A	---	23	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	7	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-20V , V_{GS}=-4.5V , I_D=-12A	---	25	---	nC
Q_{gs}	Gate-Source Charge		---	6.7	---	
Q_{gd}	Gate-Drain Charge		---	5.5	---	
Td(on)	Turn-On Delay Time	V_{DD}=-15V , V_{GS}=-10V , R_G=3.3Ω, I_D=-1A	---	38	---	ns
T_r	Rise Time		---	23.6	---	
Td(off)	Turn-Off Delay Time		---	100	---	
T_f	Fall Time		---	6.8	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	3635	---	pF
Coss	Output Capacitance		---	224	---	
Crss	Reverse Transfer Capacitance		---	141	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-35	A
ISM	Pulsed Source Current[2,5]		---	---	-70	A
VSD	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1	V

Note :

1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The EAS data shows Max. rating . The test condition is VDD=-48V,VGS =-10V,L=0.1mH,IAS =-47.6A

4、The power dissipation is limited by 150℃ junction temperature

5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

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Typical Characteristics

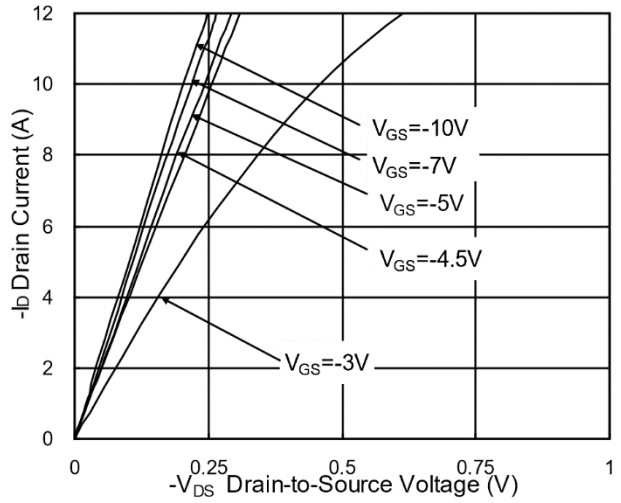

Fig.1 Typical Output Characteristics

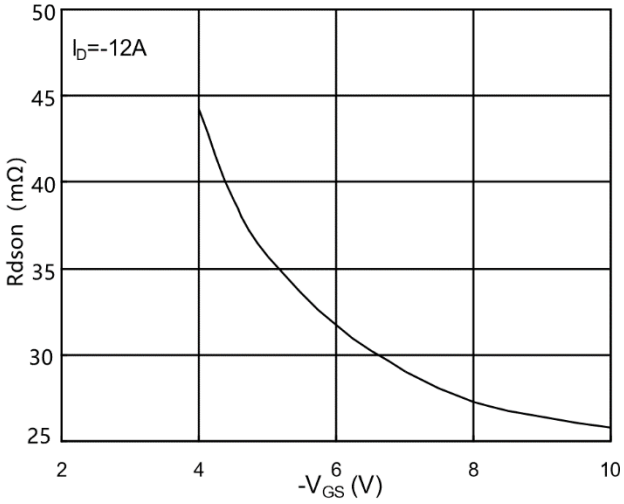

Fig.2 On-Resistance v.s Gate-Source

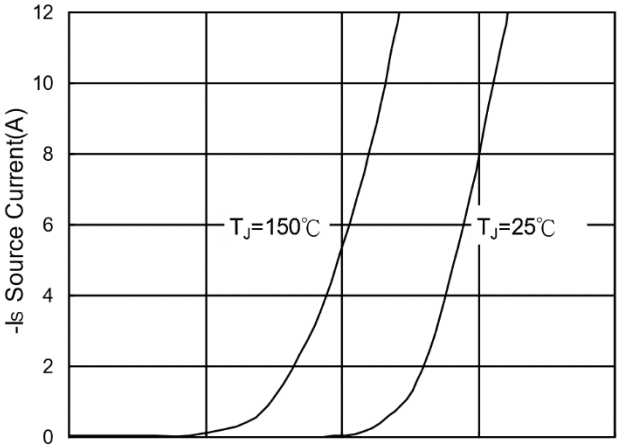

Fig.3 Forward Characteristics Of Reverse

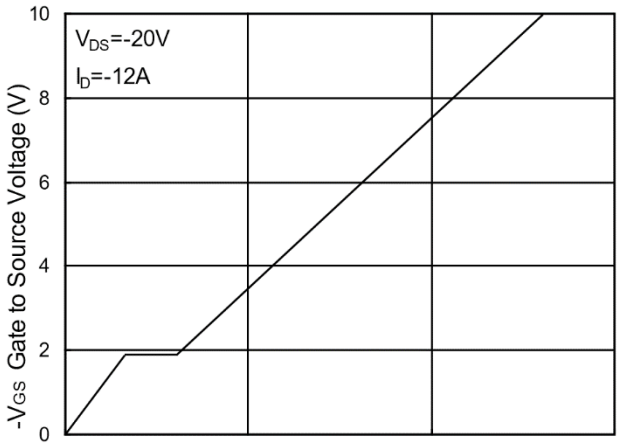

Fig.4 Gate-Charge Characteristics

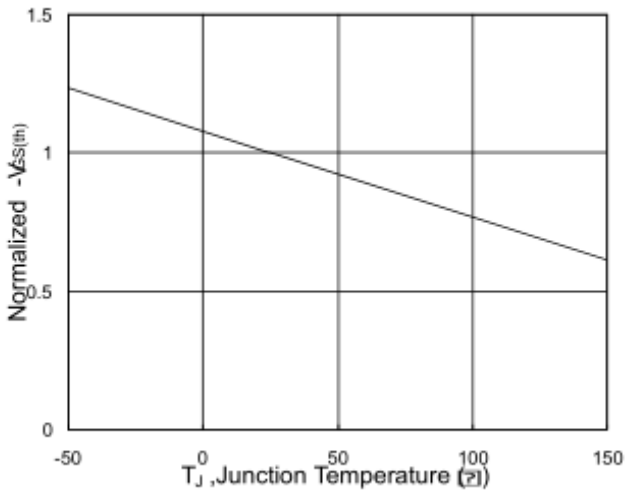

Fig.5 Normalized $V_{GS(th)}$ v.s T_J

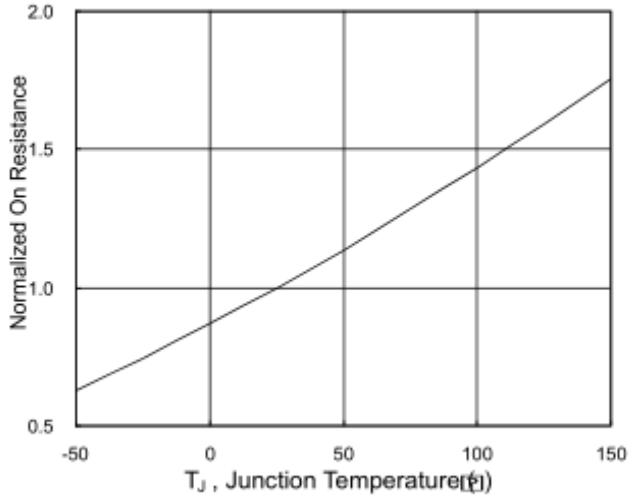

Fig.6 Normalized R_{DSON} v.s T_J

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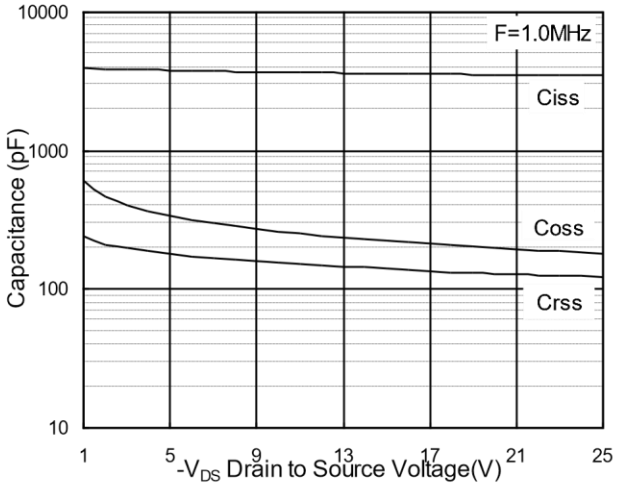


Fig.7 Capacitance

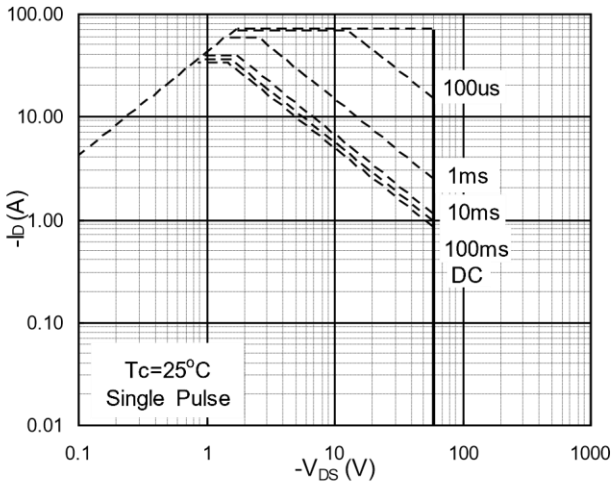


Fig.8 Safe Operating Area

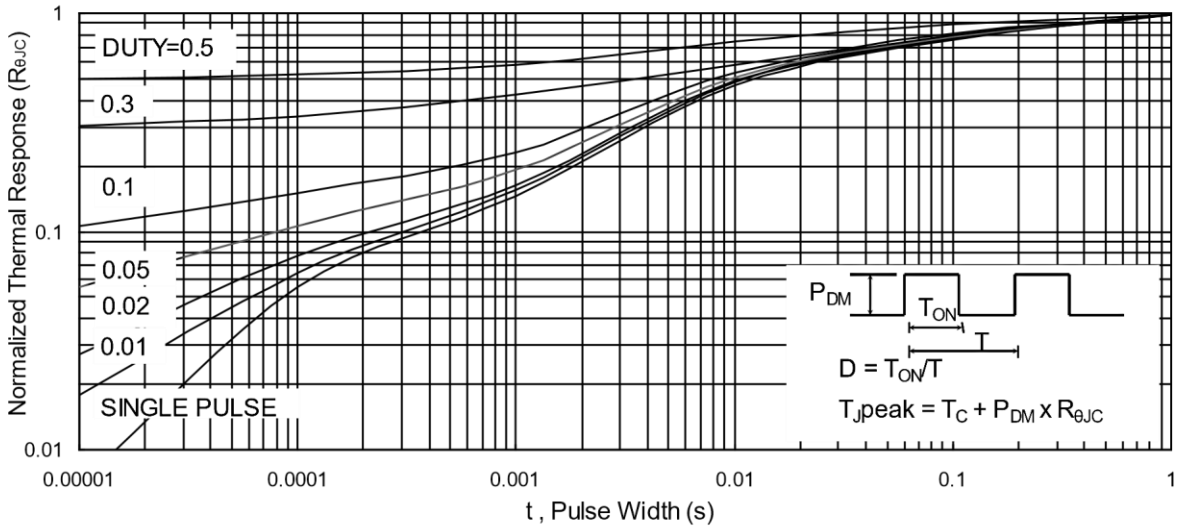


Fig.9 Normalized Maximum Transient Thermal Impedance

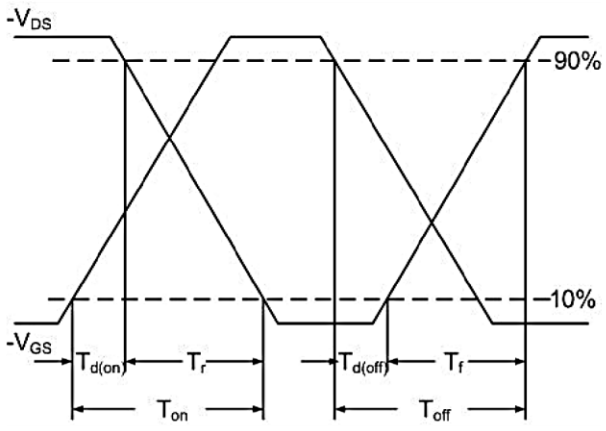


Fig.10 Switching Time Waveform

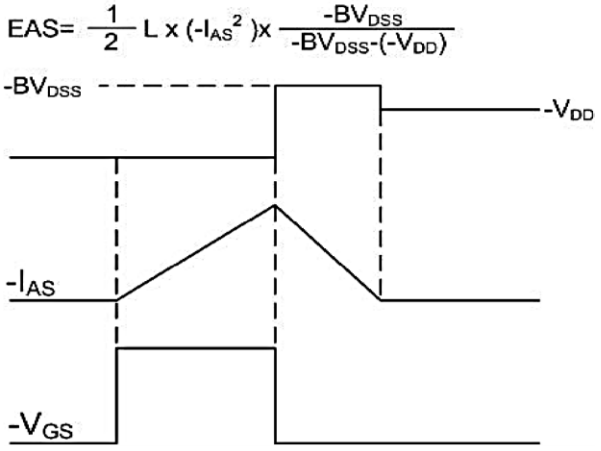
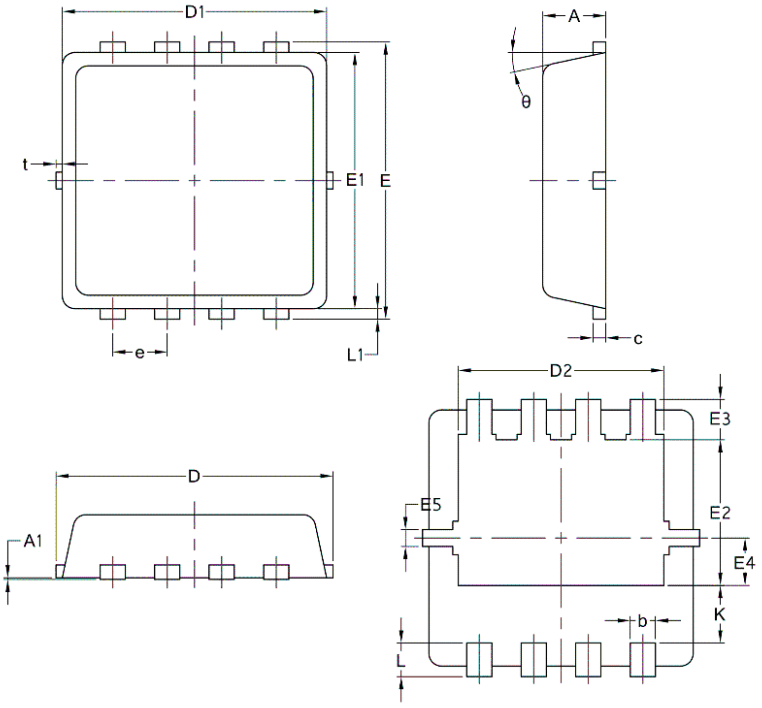


Fig.11 Unclamped Inductive Waveform

Package Mechanical Data-DFN3*3-8L-JQ Single



Symbol	Common		
	mm		
	Mim	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.20	0.30	0.40
c	0.10	0.152	0.25
D	3.15	3.30	3.45
D1	3.00	3.15	3.25
D2	2.29	2.45	2.65
E	3.15	3.30	3.45
E1	2.90	3.05	3.20
E2	1.54	1.74	1.94
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.59	0.69	0.89
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
t	0	0.075	0.13
Φ	10	12	14